

P1000A - P1000M

AXIAL LEADED SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V CURRENT: 10.0 A

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

Case: R-6, Molded Plastic

 Terminals: Plated Leads Solderable per MIL-STD-202, Method 208

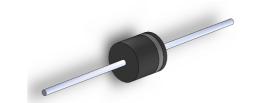
Polarity: Cathode Band

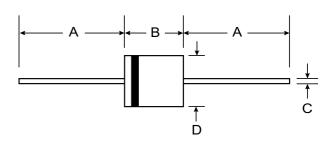
Mounting Position: Any

Marking: Type Number

Weight: 2.1 grams (approx.)







R-6						
Dim	Min	Max				
Α	25.4	_				
В	8.6	9.1				
С	1.2	1.3				
All Dimensions in mm						

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

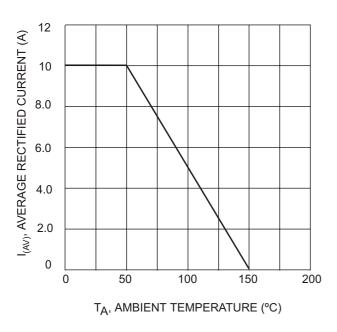
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

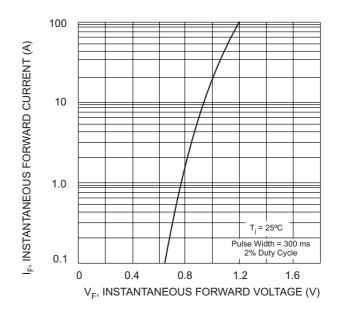
Characteristi	Symbol	P1000A	P1000B	P1000D	P1000G	P1000J	P1000K	P1000M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	٧
Average Rectified Output Current (Note 1) @T _A = 50°C	lo	10							А
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	lғsм	600						Α	
Forward Voltage @I _F = 10A	VFM	1.0						V	
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	lгм	10 100						μΑ	
Typical Junction Capacitance (Note 2)	Cj	150 80					pF		
Typical Thermal Resistance Junction to Ambient (Note 1)	$R_{ heta}$ JA	10					°C/W		
Operating Temperature Range	Tj	-50 to +150					°C		
Storage Temperature Range	Тѕтс	-50 to +150					°C		

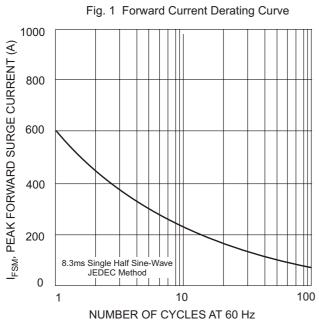
Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

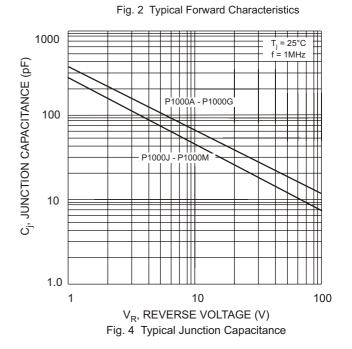








NUMBER OF CYCLES AT 60 Hz
Fig. 3 Maximum Non-Repetitive Peak Forward Surge Current



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